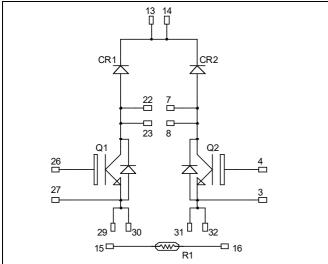
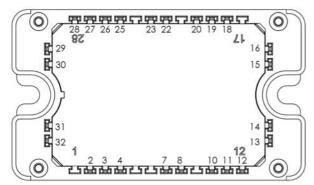


Dual Boost chopper Trench + Field Stop IGBT4 Power module







All multiple inputs and outputs must be shorted together Example: 13/14; 29/30; 22/23 ...

Application

- AC and DC motor control
- Switched Mode Power Supplies
- Power Factor Correction

Features

- Trench + Field Stop IGBT 4
 - Low voltage drop
 - Low leakage current
 - Low switching losses
 - Low leakage current
 - RBSOA and SCSOA rated
- Kelvin emitter for easy drive
- Very low stray inductance
- Internal thermistor for temperature monitoring

Benefits

- Outstanding performance at high frequency operation
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Solderable terminals both for power and signal for easy PCB mounting
- Low profile
- Easy paralleling due to positive TC of VCEsat
- Each leg can be easily paralleled to achieve a single boost of twice the current capability
- RoHS compliant

All ratings @ $T_j = 25^{\circ}C$ unless otherwise specified

Absolute maximum ratings (per IGBT)

INDUITE	e maximum racings (per 1881)			
Symbol	Parameter		Max ratings	Unit
V_{CES}	Collector - Emitter Voltage		1200	V
Ţ	Continuous Collector Current	$T_c = 25^{\circ}C$	110	
$I_{\rm C}$	Continuous Collector Current	$T_c = 80$ °C	90	A
I_{CM}	Pulsed Collector Current	$T_c = 25^{\circ}C$	150	
V_{GE}	Gate – Emitter Voltage		±20	V
P_D	Power Dissipation	$T_c = 25$ °C	385	W
RBSOA	Reverse Bias Safe Operating Area	$T_{\rm j} = 150^{\circ}{\rm C}$	150A @ 1150V	

CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed.

Electrical Characteristics (per IGBT)

Symbol	Characteristic	Test Conditions		Min	Typ	Max	Unit
I_{CES}	Zero Gate Voltage Collector Current	$V_{GE} = 0V ; V_{CE} = 1200V$				250	μΑ
17	Callactor Emitter Seturation Valtage	$V_{GE} = 15V$	$T_j = 25^{\circ}C$		1.85	2.25	V
$V_{CE(sat)}$	Collector Emitter Saturation Voltage	$I_C = 75A$	$T_j = 150$ °C		2.25		ľ
$V_{GE(th)}$	Gate Threshold Voltage	$V_{GE} = V_{CE}, I_C = 3 \text{ mA}$		5	5.8	6.5	V
I_{GES}	Gate – Emitter Leakage Current	$V_{GE} = 20 \text{ V}, V_{CE} = 0 \text{ V}$				600	nA

Dynamic Characteristics (per IGBT)

Symbol	Characteristic	Test Conditions		Min	Typ	Max	Unit
Cies	Input Capacitance	$\begin{array}{c} V_{GE} = 0V \\ V_{CE} = 25V \\ f = 1MHz \end{array}$			4.4		
Coes	Output Capacitance				0.29		nF
C_{res}	Reverse Transfer Capacitance				0.24		
Q_{G}	Gate charge	$V_{GE} = \pm 15V ; V_{GE} = 15V ; V_$	$V_{GE} = \pm 15V ; V_{CE} = 600V$ $I_{C} = 75A$		0.57		μС
T _{d(on)}	Turn-on Delay Time	Inductive Switc	hing (25°C)		130		ns
$T_{\rm r}$	Rise Time	$V_{GE} = \pm 15V$			20		
$T_{d(off)}$	Turn-off Delay Time	$V_{\text{Bus}} = 600V$ $I_{\text{C}} = 75A$			300		
T_{f}	Fall Time	$R_G = 2.2\Omega$			45		
$T_{d(on)}$	Turn-on Delay Time		Inductive Switching (150°C) $V_{GE} = \pm 15V$ $V_{Dec} = 600V$		150		ns
T_{r}	Rise Time	$V_{GE} = \pm 15 V$ $V_{Bus} = 600 V$			35		
$T_{d(off)}$	Turn-off Delay Time	$I_C = 75A$			350		
T_{f}	Fall Time	$R_G = 2.2\Omega$			80		
Eon	Turn-on Switching Energy	$V_{GE} = \pm 15V$	$T_J = 25$ °C		3.3		mJ
Lon	$V_{\text{Bus}} = 600V \qquad T_{\text{J}} = 150^{\circ}\text{C}$		8.5		1113		
E_{off}	Turn-off Switching Energy	$I_C = 75A$	$T_J = 25$ °C		4.2		mJ
Lom	Turn on Switching Energy	$R_G = 2.2\Omega$	$T_J = 150$ °C		7.2		1113
I_{sc}	Short Circuit data	$V_{GE} \le 15V ; V_{Bu}$ $t_p \le 10 \mu s ; T_j = 1$			300		A
R_{thJC}	Junction to Case Thermal Resistance					0.39	°C/W

Chopper diode ratings and characteristics (per diode)

Symbol	Characteristic Test Conditions		Min	Typ	Max	Unit	
V_{RRM}	Peak Repetitive Reverse Voltage					1200	V
I_{RM}	Reverse Leakage Current	$V_R = 1200V$				100	μΑ
I_F	DC Forward Current		$Tc = 80^{\circ}C$		100		A
		$I_F = 100A$	= 100A		2.4	3	
V_{F}	Diode Forward Voltage	$I_F = 150A$			2.7		V
		$I_F = 100A$	$T_j = 125$ °C		1.8		
+	t_{rr} Reverse Recovery Time $I_F = 100 A$	$T_j = 25$ °C		385		n a	
ι_{rr}		$I_F = 100A$ - $V_R = 800V$	$T_j = 125$ °C		480		ns
Qrr	Reverse Recovery Charge	$\frac{1}{di} = \frac{1}{di} $	$T_j = 25$ °C	1055		C	
			$T_j = 125$ °C		5240		пC
R_{thJC}	Junction to Case Thermal Resistance					0.55	°C/W



Thermal and package characteristics

Symbol	Characteristic			Min	Max	Unit
V_{ISOL}	RMS Isolation Voltage, any terminal to case t = 1 min, 50/60Hz			4000		V
T_{J}	Operating junction temperature range			-40	175	
T_{JOP}	Recommended junction temperature under s	witching condit	ions	-40	T _J max -25	°C
T_{STG}	Storage Temperature Range			-40	125	
$T_{\rm C}$	Operating Case Temperature			-40	125	
Torque	Mounting torque	To heatsink	M4	2	3	N.m
Wt	Package Weight			110	g	

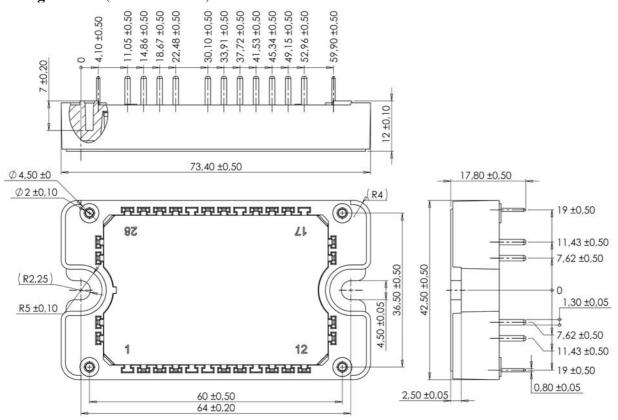
Temperature sensor NTC (see application note APT0406 on www.microsemi.com for more information).

Symbol	Characteristic		Min	Typ	Max	Unit
R ₂₅	Resistance @ 25°C			50		kΩ
$\Delta R_{25}/R_{25}$				5		%
B _{25/85}	$T_{25} = 298.15 \text{ K}$			3952		K
$\Delta \mathrm{B/B}$		T _C =100°C		4		%

$$R_T = \frac{R_{25}}{\exp \left[B_{25/85} \left(\frac{1}{T_{25}} - \frac{1}{T} \right) \right]} \quad \text{T: Thermistor temperature}$$

$$R_T: \text{ Thermistor value at T}$$

Package outline (dimensions in mm)

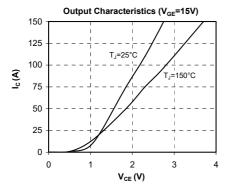


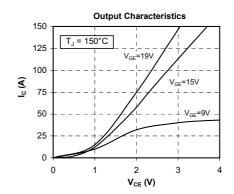
See application note 1906 - Mounting Instructions for SP3F Power Modules on www.microsemi.com

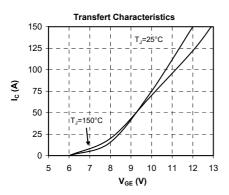
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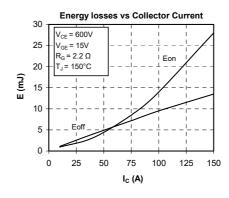


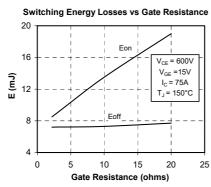
Typical Performance Curve

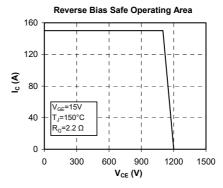


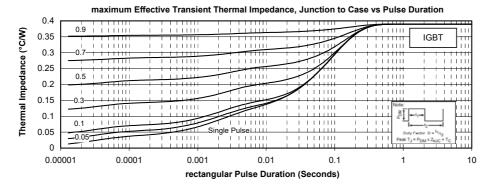




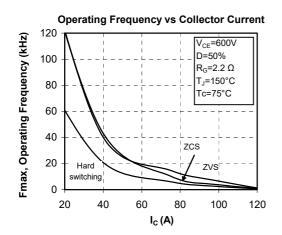


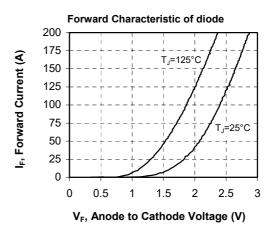


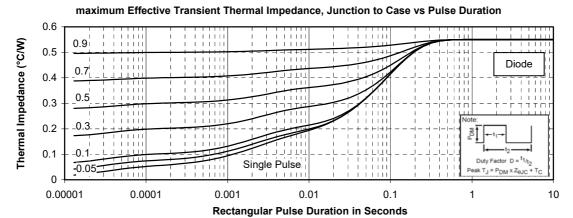












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